TOSHIBA TLP741G

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-THYRISTOR

TLP741G

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
SOLID STATE RELAY
SWITCHING POWER SUPPLY

The TOSHIBA TLP741G consists of a photo-thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

Peak Off-State Voltage : 400V (Min.)
 Trigger LED Current : 10mA (Max.)
 On-State Current : 150mA (Max.)

• UL Recognized : UL1577, File No. E67349

• BSI Approved : BS EN60065:1994

Certificate No. 6617 BS EN60950:1992 Certificate No. 7366

• Isolation Voltage : $4000V_{rms}$ (Min.)

Option (D4) type

VDE Approved : DIN VDE0884/08, 87

Certificate No. 65640

Maximum Operating Insulation Voltage : $630V_{PK}$ Highest Permissible Over Voltage : $6000V_{PK}$

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

7.62mm pich 10.16mm pich standard type (LF2) type

Creepage Distance : 7.0mm (Min.) 8.0mm (Min.)
 Clearance : 7.0mm (Min.) 8.0mm (Min.)

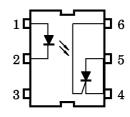
Insulation Thickness : 0.5mm (Min.) 0.5mm (Min.)

11-7B1

Weight: 0.35g

TOSHIBA

PIN CONFIGURATIONS (TOP VIEW)



1: ANODE

2 : CATHODE

3: NC

4 : CATHODE

5: ANODE

6 : **GATE**

MAXIMUM RATINGS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	RATING	UNIT
LED	Forward Current	$I_{\mathbf{F}}$	60	mA
	Forward Current Derating (Ta≥39°C)	ΔI _F /°C	-0.7	mA/°C
	Peak Forward Current (100 µs pulse, 100 pps)	I_{FP}	1	A
	Power Dissipation	$P_{\mathbf{D}}$	100	mW
	Power Dissipation Derating (Ta≥25°C)	$\Delta P_{\mathbf{D}}/^{\circ}C$	-1.0	mW/°C
	Reverse Voltage	v_{R}	5	V
	Junction Temperature	T_j	125	°C
	Peak Forward Voltage ($R_{GK} = 27k\Omega$)	$v_{ m DRM}$	400	V
	Peak Reverse Voltage ($R_{GK} = 27k\Omega$)	V_{RRM}	400	V
	On-State Current	I _{T (RMS)}	150	mA
OR	On-State Current Derating (Ta≥25°C)	ΔI _T /°C	-2.0	mA/°C
DETECT	Peak On-State Current (100 μ s pulse, 120pps)	I _{TP}	3	A
ΤE	Peak One Cycle Surge Current	I_{TSM}	2	A
DE	Peak Reverse Gate Voltage	v_{GM}	5	V
	Power Dissipation	$P_{\mathbf{D}}$	150	mW
	Power Dissipation Derating (Ta≥25°C)	$\Delta P_{\mathbf{D}}/^{\circ}C$	-2.0	mW/°C
	Junction Temperature	T_{j}	100	°C
Sto	rage Temperature Range	$T_{ m stg}$	-55~125	°C
Оре	rating Temperature Range	$T_{ m opr}$	-55~100	°C
Lea	d Soldering Temperature (10s)	T _{sol}	260	°C
Tot	al Package Power Dissipation	PT	250	mW
	al Package Power Dissipation Derating ≥ 25°C)	ΔP _T /°C	-3.3	mW/°C
Isol	ation Voltage (AC, 1 min., R.H.≤60%)	BV_S	4000	V _{rms}

RECOMMENDED OPERATING CONDITIONS

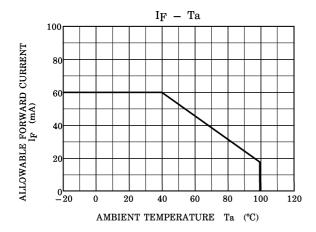
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	v_{AC}	_	_	120	Vac
Forward Current	$I_{\mathbf{F}}$	15	20	25	mA
Operating Temperature	$T_{ m opr}$	-25	_	85	°C
Gate to Cathode Resistance	R_{GK}	_	27	33	$\mathbf{k}\Omega$
Gate to Cathode Capacity	c_{GK}	_	0.01	0.1	$\mu \mathbf{F}$

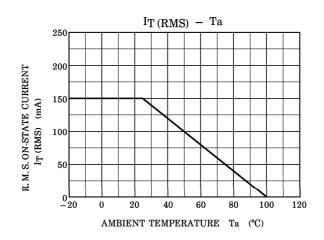
INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

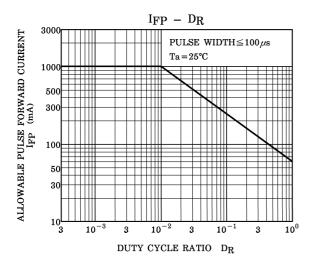
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	$V_{\mathbf{F}}$	I _F =10mA		1.0	1.15	1.3	V
	Reverse Current	$I_{\mathbf{R}}$	$V_R=5V$		_	_	10	μ A
	Capacitance	C_{T}	V=0, f=1MHz		_	30	_	pF
DETECTOR	Off-State Current	$I_{ m DRM}$	$V_{AK} = 400V$	Ta=25°C	_	10	5000	nA
			$R_{GK} = 27k\Omega$	Ta=100°C	_	1	100	μ A
	Reverse Current	I_{RRM}	$V_{KA} = 400V$	Ta=25°C	_	10	5000	nA
			$R_{GK} = 27k\Omega$	Ta=100°C	_	1	100	μ A
	On-State Voltage	$ m V_{TM}$	$I_{TM} = 100 mA$		_	0.9	1.3	V
	Holding Current	${ m I_H}$	$R_{GK} = 27k\Omega$		_	0.2	_	mA
	Off-State dv/dt	dv / dt	V_D =280V, R_{GK} =27k Ω		5	10	_	$V/\mu s$
	Capacitance C _j	C.	V=0, f=1MHz	Anode to Gate	_	20	_	Tr
		v = 0, 1 = 1MH2	Gate to Cathode	_	350	_	pF	

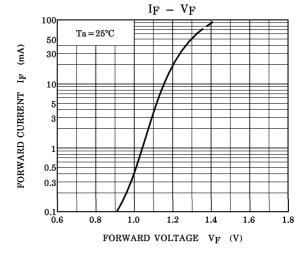
COUPLED CHARACTERISTICS (Ta = 25°C)

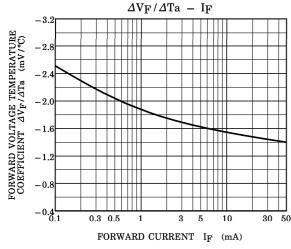
CHARACTERISTIC	SYMBOL	TEST CONDITION		TYP.	MAX.	UNIT	
Trigger LED Current	I_{FT}	$V_{AK}=6V, R_{GK}=27k\Omega$	_	4	10	mA	
Turn-on Time	$t_{ m ON}$	I_{F} =30mA, V_{AA} =50V, R_{GK} =27k Ω	_	10	_	μ s	
Coupled dv/dt	dv / dt	V_S =500V, R_{GK} =27k Ω	500			V/μs	
Capacitance (Input to Output)	c_{S}	$V_S=0$, $f=1MHz$	_	0.8	_	pF	
Isolation Resistance	$R_{\mathbf{S}}$	$V_S = 500V$	1×10^{12}	10^{14}	_	Ω	
		AC, 1 minute	4000 —		37		
Isolation Voltage	$^{ m BV}_{ m S}$	AC, 1 second, in oil	_	10000	_	$\left V_{ m rms} \right $	
		DC, 1 minute, in oil	_	10000	_	v_{dc}	

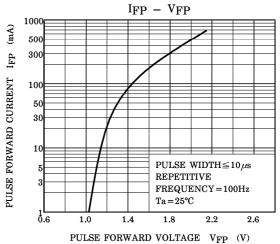


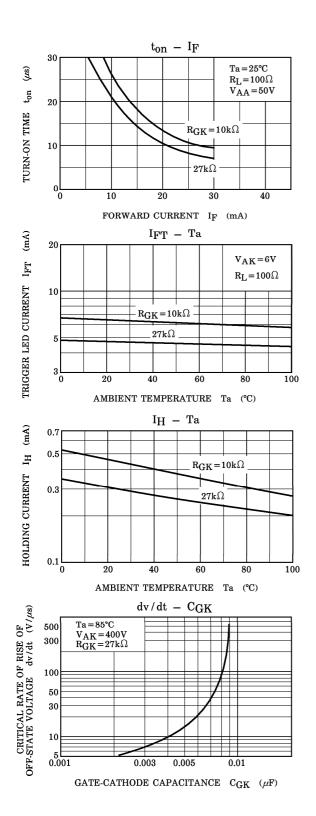


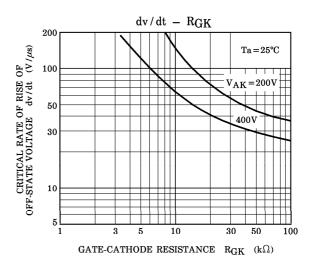


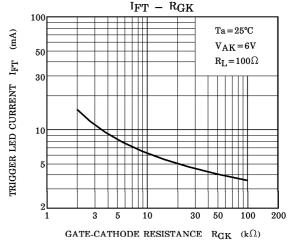


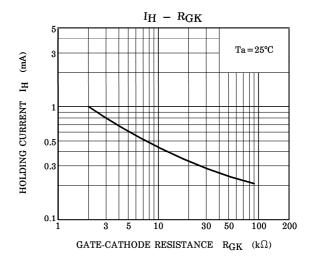












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